Claim 16. (original) The method of claim 9, wherein after the step of forming a channel layer over the insulation layer, further includes forming an ohmic contact layer over the channel layer.

Canceled

Claim 17. (~~withdrawn~~) A pixel structure over a substrate, the pixel structure comprising:

a thin film transistor over the substrate, the thin film transistor having a gate, a channel layer and a pair of source/drain terminals;

a scan line over the substrate, the scan line and the gate being electrically connected;

a data line over the substrate, the data line and the source terminal being electrically connected;

an insulation layer over the substrate only in areas having the gate, the source/drain terminals, the data line and the scan line thereon, and the insulation layer covering the gate and the scan line;

a passivation layer over the substrate only in areas having the gate, the source/drain terminals, the data line and the scan line, and the passivation layer covering the source/drain terminals and the data line, wherein a sidewall of the source/drain terminal is exposed; and

a pixel electrode over the substrate, the pixel electrode being positioned close to the thin film transistor such that the pixel electrode and a sidewall of the drain terminal of the thin film transistor are electrically connected.

Canceled

Claim 18. (~~withdrawn~~) The pixel structure of claim 17, wherein the pixel structure further include a conductive structure within the passivation layer such that the pixel electrode and the

drain terminal are electrically connected through the conductive structure as well as the sidewall of the drain terminal.

Canceled

Claim 19. (~~withdrawn~~) The pixel structure of claim 17, wherein the pixel structure further include a conductive layer over a scan line neighboring the original scan line such that the conductive layer, the neighboring scan line and the insulation layer between the conductive layer and the neighboring scan line together form a pixel storage capacitor.

Canceled

Claim 20. (~~withdrawn~~) The pixel structure of claim 19, wherein a sidewall of the conductive layer is electrically connected to the pixel electrode.

Canceled

Claim 21. (~~withdrawn~~) The pixel structure of claim 19, wherein the pixel structure further include a metallic pad near the edge of the substrate such that the metallic pad and the data line are electrically connected and that the pixel electrode and a sidewall of the metallic pad are electrically connected.

Canceled

Claim 22. (~~withdrawn~~) The pixel structure of claim 19, wherein the pixel structure further include a metallic pad near the edge of the substrate such that the metallic pad and the scan line are electrically connected and that the pixel electrode and a sidewall of the metallic pad are electrically connected.

Canceled

Claim 23. (~~withdrawn~~) The pixel structure of claim 19, wherein the pixel structure further include an ohmic contact layer over the channel layer.

Canceled

Claim 24. (~~withdrawn~~) The pixel structure of claim 19, wherein the pixel structure further include an etching stop layer over the channel layer.